

WST5035AN-L**Smart High-Side Power Switch Single Channel, 35mΩ, DFN9×6-14L , AEC-Q100 qualified****Application**

- ◆ Suitable for resistive, inductive and capacitive loads
- ◆ Replaces electromechanical relays, fuses and discrete circuits
- ◆ Most suitable for loads with high inrush current, such as lamps
- ◆ Suitable for 24V and 48V trucks + trailer and transportation systems

Basic Features

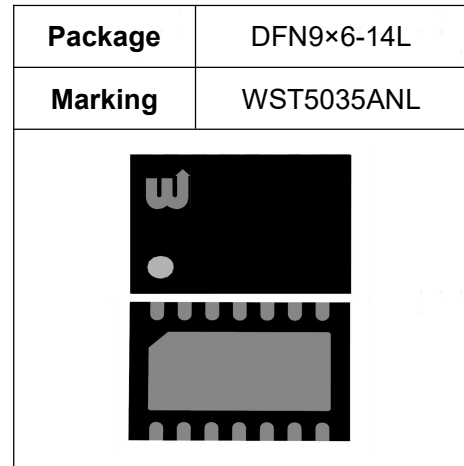
- ◆ PRO-SIL™ ISO 26262-ready for supporting the integrator in evaluation of hardware element according to ISO 26262:2018 Clause 8-13
- ◆ Single channel device
- ◆ Very low stand-by current
- ◆ 3.3 V and 5 V compatible logic inputs
- ◆ Optimized electromagnetic compatibility
- ◆ Very low electromagnetic susceptibility
- ◆ Adjustable current limitation

Diagnostic Functions

- ◆ Off-state open load detection
- ◆ OUT short to VS detection
- ◆ Overload and short to ground latch-off
- ◆ Thermal shutdown latch-off

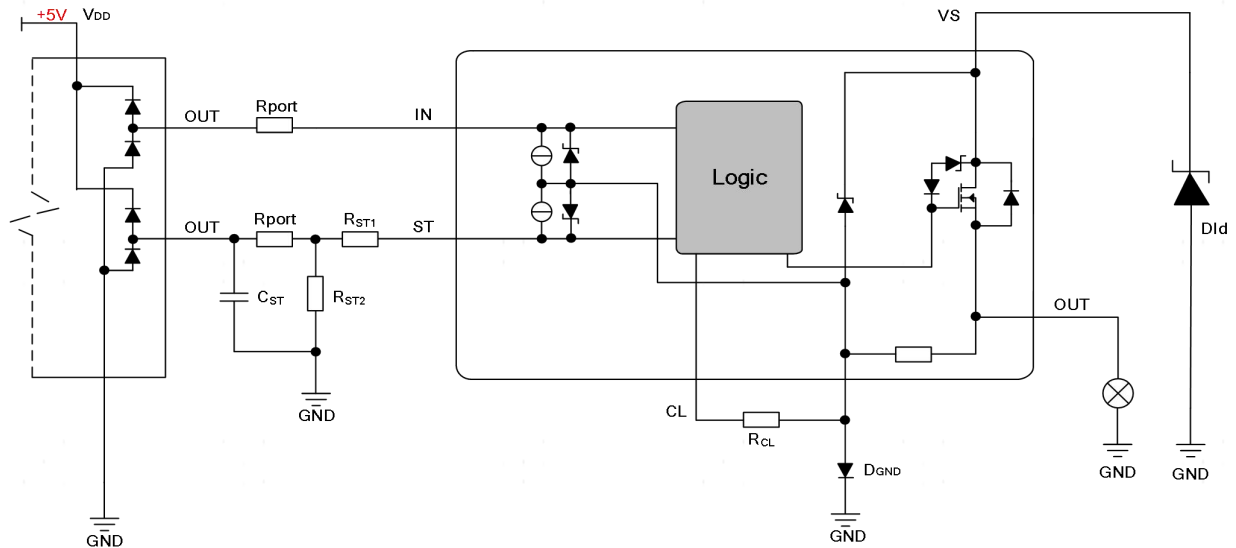
Protection Functions

- ◆ Undervoltage shutdown
- ◆ Overvoltage clamp
- ◆ Load current limitation
- ◆ Self limiting of fast thermal transients
- ◆ Protection against loss of ground and loss of VS
- ◆ Thermal shutdown

**Product Summary**

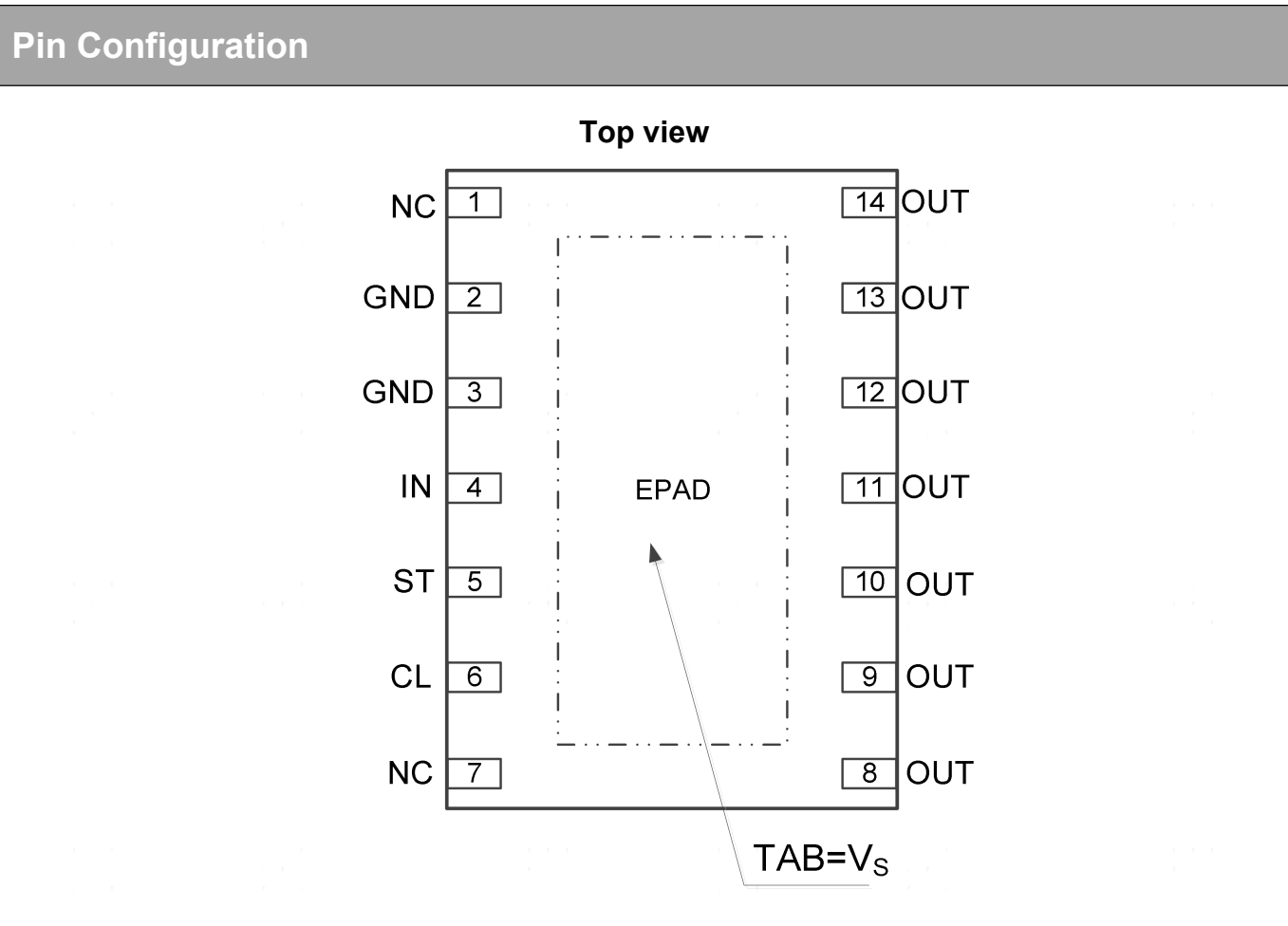
Parameter	Symbol	Value
Max. transient supply voltage	V_S	70V
Operating voltage range	V_{NOM}	5-58V
On-state resistance ($T_j = 25^\circ\text{C}$)	R_{ON}	35mΩ
Nominal load current ($T_j = 25^\circ\text{C}$)	$I_{L(NOM)}$	7A
Current limitation	I_{LIMH}	Adjustable
Supply current in sleep	I_{SLEEP}	5uA

Typical Application Circuit



Note1: For D_{GND} , the diode with lower V_F is advisable.

Ordering Information		
Package	Top Mark	Part No.
DFN9×6-14L, Pb-free	WST5035ANL XXYMXX	WST5035AN-L



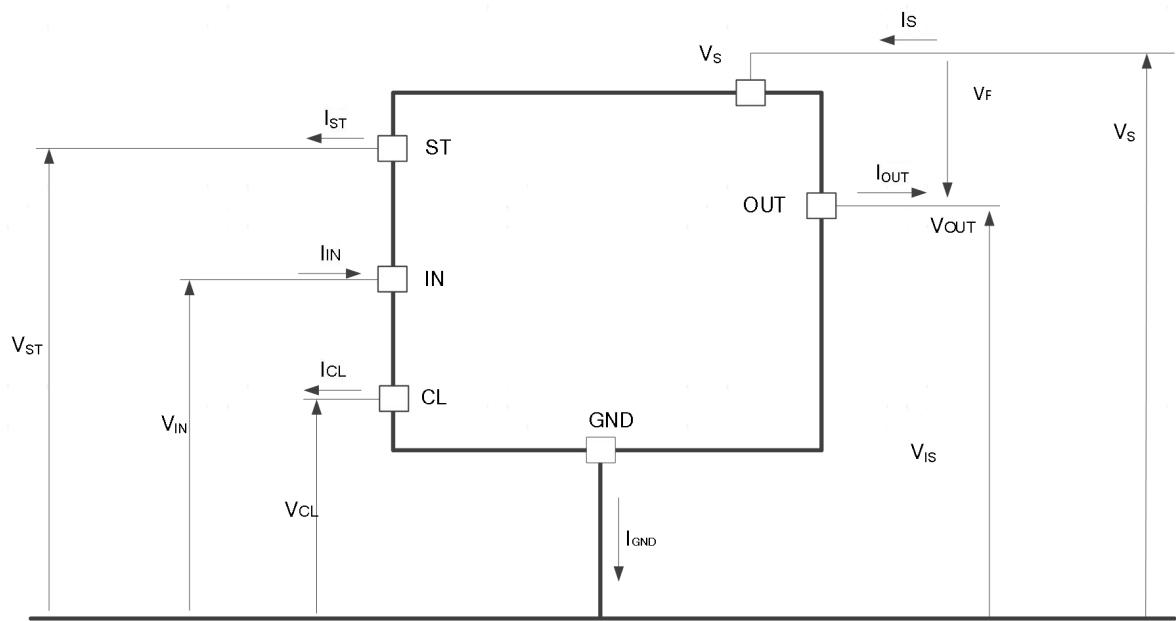
Pin Description		
Pin Name	Pin NO.	Pin Description
NC	1/7	Not Connected
GND	2/3	Ground connection. Must be reverse battery protected by an external diode.
IN	4	Voltage controlled input pin with hysteresis, compatible with 3 V and 5 V CMOS outputs. It controls output switch state.
ST	5	Diagnostic feedback of channel.
CL	6	Adjustable current limit, floating if external current limit is not need.
OUT	8/9/10/11/12/13/14	Power outputs.
VS	EPAD	Battery connection.

Table 1. Suggested connections for unused and not connected pins

Connection / pin	OUT	IN
Floating	X ⁽¹⁾	X
To ground	Not allowed	Through 15K resistor

Note2: X do not care.

Current and Voltage Conventions



Note3: $V_F = V_{OUT} - V_S$ during reverse battery condition.

Absolute Maximum Ratings (Note3)

Symbol	Parameter	Value	Unit
V_s	Transient supply voltage	65	V
$-V_s$	Reverse DC supply voltage	0.3	V
$-I_{GND}$	DC reverse ground pin current	200	mA
I_{OUT}	OUT DC output current	Internally limited	A
V_{IN}, V_{CL}, V_{ST}	IN, CL, ST DC input voltage	-0.3 to 6.0	V
T_j	Junction operating temperature	-40 to 150	°C
T_{stg}	Storage temperature	-55 to 150	

Note4: Stressing the device above the rating listed in Absolute maximum ratings may cause permanent damage to the device. These are stress ratings only and operation of the device at these or any other conditions above those indicated in the operating sections of this specification is not implied.

Exposure to the conditions in table below for extended periods may affect device reliability.

Thermal Resistance (Note4)

Symbol	Parameter	Value	Unit
T_{JC}	Thermal Resistance Junction-to-Case	1.3	°C/W
T_{JA}	Junction-to-Ambient Thermal Resistance	30	°C/W

Note5: According to JEDEC JESD51-2,-5,-7 at natural convection on FR4 2s2p board; the Product (Chip + Package) was simulated on a 76.2 × 114.3 × 1.5 mm board with 2 inner copper layers (2 × 70 μm Cu, 2 × 35 μm Cu). Where applicable a thermal via array under the exposed pad contacted the first inner copper layer.

ESD Susceptibility (Note5)

Symbol	Parameter	Values	Unit
$V_{ESD(HBM)}^{(3)}$	ESD Susceptibility all Pins (HBM)	± 2	kV
$V_{ESD(HBM)_{OUT}}$	ESD Susceptibility OUT vs GND and V_S connected (HBM)	± 4	kV
$V_{ESD(CDM)}^{(4)}$	ESD Susceptibility all Pins (CDM)	± 500	V
$V_{ESD(CDM)_{CORN}}$	ESD Susceptibility Corner Pins (CDM) (pins 1, 7, 8, 14)	± 750	V

Note6:

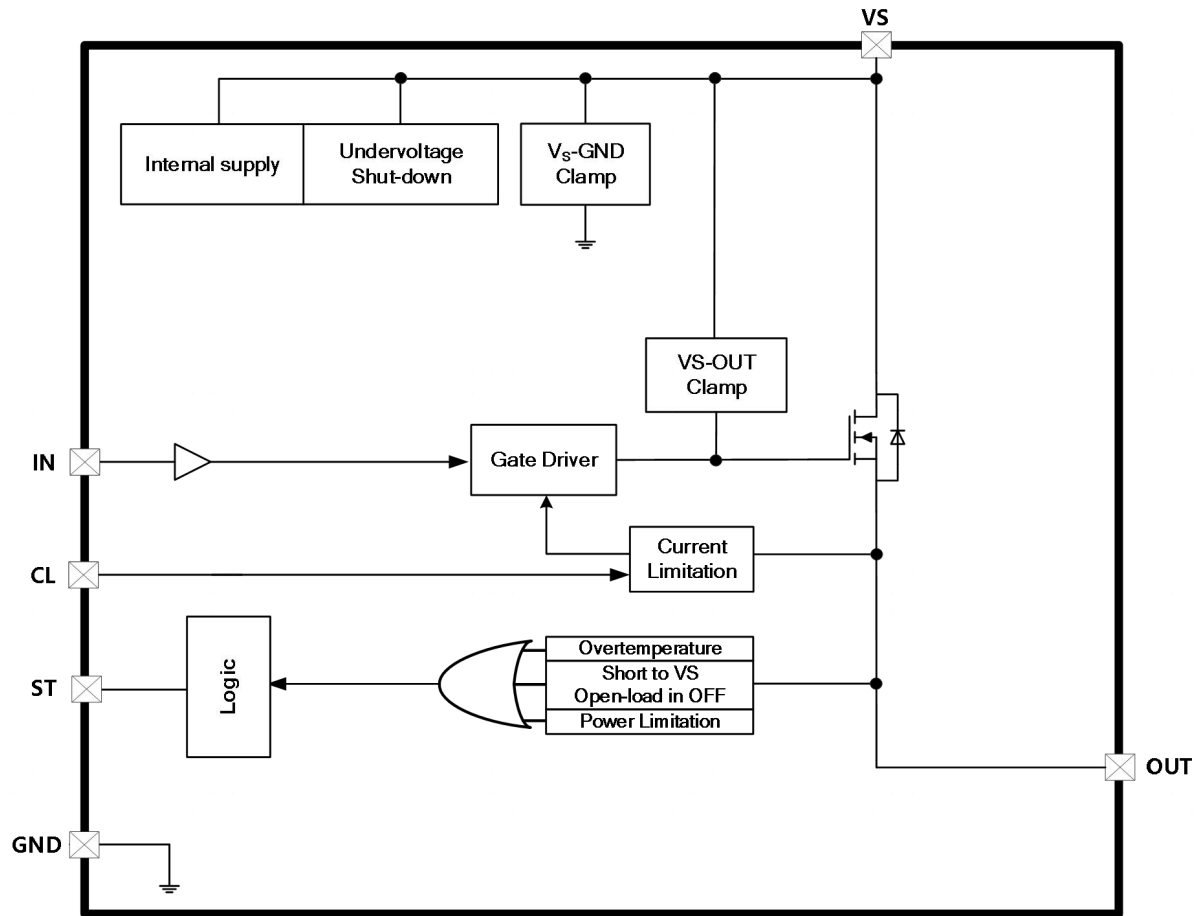
- 1) Not subject to production test - specified by design.
- 2) Maximum digital input voltage to be considered for Latch-Up tests: 5.5 V.
- 3) ESD susceptibility, Human Body Model "HBM", according to AEC Q100-002.
- 4) ESD susceptibility, Charged Device Model "CDM", according to AEC Q100-011.

EAS Susceptibility (Note6)

Symbol	Parameter	Values			Unit	Note or Test Conditon
		Min.	Typ.	Max.		
E_{AS}	Maximum Energy Dissipation Single Pulse			120	mJ	$I_{OUT} = 7A$ $T_{J(0)} = 150\text{ }^{\circ}C$ $V_S = 28\text{ V}$

Note7:: Not subject to production test - specified by design.

Functional Block



Electrical Characteristics (Note8), $8V < V_S < 36V$; $-40^{\circ}C < T_J < 150^{\circ}C$, unless otherwise specified**Power section**

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Nominal operating voltage	V_{NOM}		5	48	58	V
Under voltage shutdown	V_{USD}			3.5	5.0	V
Under voltage shutdown hysteresis	$V_{USDhyst}$			0.3		V
On-state resistance	R_{ON}	$I_{OUT}=2A, T_J = 25^{\circ}C$		35		mΩ
		$I_{OUT}=2A, T_J = 150^{\circ}C$			70	
		$I_{OUT}=2A, V_S=5V, T_J = 25^{\circ}C$			55	
Nominal load current	$I_{L(NOM)}$	$T_A=25^{\circ}C$		7		A
Nominal load current at $T_A=85^{\circ}C$	$I_{L(NOM)_85}$	$T_A=85^{\circ}C, T_J < 150^{\circ}C$		5		A
Inverse Current Capability	$I_{L(INV)}$	$V_S < V_{OUT}, V_{IN}=5V, T_A=25^{\circ}C$		7		A
V_S clamp voltage	V_{CLAMP}	$I_S=5mA$	70	75		V
Supply current in sleep	I_{SLEEP}	$V_S=48V, V_{IN}=V_{OUT}=0V,$ $T_J=25^{\circ}C$		5.0	10	μA
		$V_S=48V, V_{IN}=V_{OUT}=0V,$ $T_J=125^{\circ}C$			25	μA
Control stage current consumption in ON state	$I_{GND(ON)}$	$V_S=48V, V_{IN}=5V$		8.0	16	mA
Off-state output current	$I_{L(off)}$	$V_{IN}=V_{OUT}=0V, V_S=48V, T_J=25^{\circ}C$		10	20	μA
		$V_{IN}=V_{OUT}=0V, V_S=48V, T_J=125^{\circ}C$			50	μA
OUT - V_S diode voltage	V_F	$I_{OUT}=-2A, T_J=150^{\circ}C$			0.9	V

Switching

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Turn-on delay time at $T_J = 25^{\circ}C$	$T_{d(on)}$	$V_S=48V, R_L=24\Omega$		15	60	us
Turn-off delay time at $T_J = 25^{\circ}C$	$T_{d(off)}$			25	80	us
Turn-on voltage slope at $T_J = 25^{\circ}C$	$(dV_{OUT}/dt)_{on}$	$V_S=48V, R_L=24\Omega$	0.5	1.2	2.5	V/us
Turn-off voltage slope at $T_J = 25^{\circ}C$	$(dV_{OUT}/dt)_{off}$		0.5	1.5	3.0	
Differential pulse skew ($t_{PHL} - t_{PLH}$)	t_{SKEW}	$V_S=48V, R_L=24\Omega$	-50		50	us

Logic input (IN, DEN)

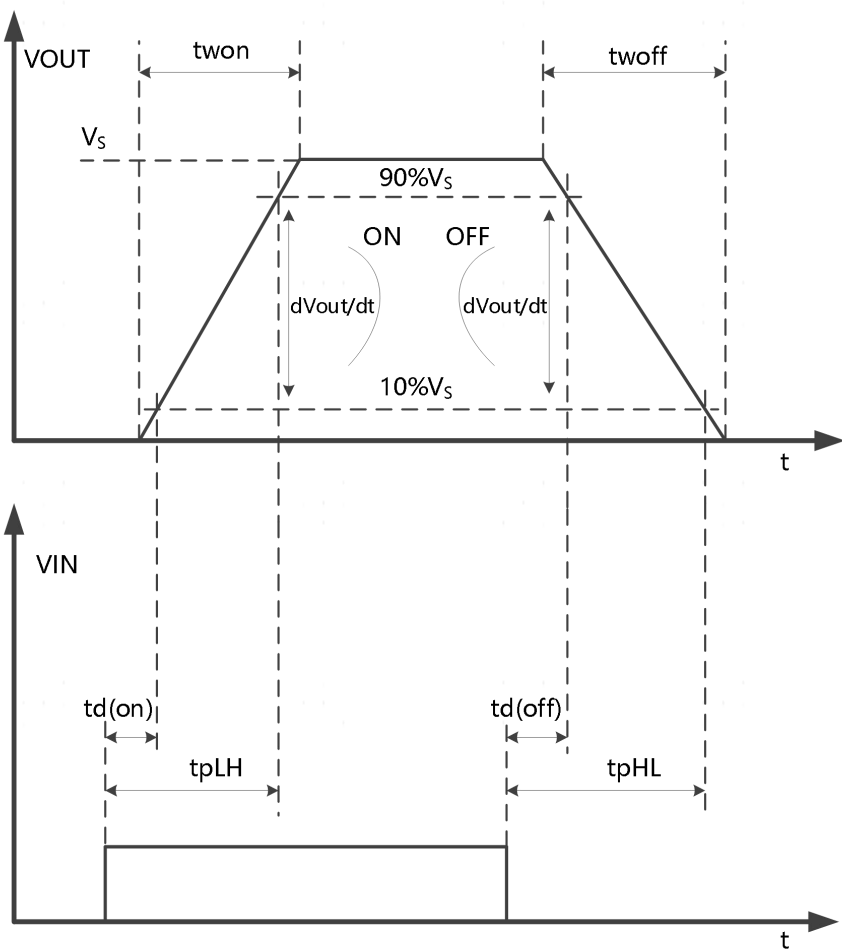
Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Logic input low level voltage	V_{LOW}				0.9	V
Low level logic input current	I_{LOW}	$V_{LOW}=0.9V$	2	11	35	μA
Logic input high level voltage	V_{HIGH}		2.1		6.0	V
High level logic input current	I_{HIGH}	$V_{HIGH}=2.0V$	1	10	32	μA
Logic input hysteresis voltage	$V_{(hyst)}$		-	0.2	-	V
ST low voltage	V_{ST}	$I_{ST} = +1.6mA$			0.6	V

Protections						
Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
CL-pin voltage V_{CL} (in ON- state)	V_{CL}	$V_S=48V, V_{IN}=5V$	0.57	0.6	0.63	V
Allowed I_{CL} range for adjusting current limit threshold	$I_{CL-range}$	$V_S=48V, V_{IN}=5V$	5		150	μA
CL short to device ground current	$I_{CL-short}$	$V_S=48V, V_{IN}=5V$	-50%	360	+50%	μA
DC short circuit current	I_{LIMH}	$5V < V_S < 36V$	8	12	16	A
		$V_S=48V, V_{IN}=5V, R_{CL}=8.2K$	-20%	9	+20%	
		$V_S=48V, V_{IN}=5V, R_{CL}=12K$	-20%	6.5	+20%	
		$V_S=48V, V_{IN}=5V, R_{CL}=24.9K$	-20%	4	+20%	
		$V_S=48V, V_{IN}=5V, R_{CL}=120K$	-20%	2.5	+20%	
Short circuit current during thermal cycling	I_{LIML}	$V_S=48V, V_{IN}=5V, T_R < T_J < T_{TSD}$		3		
Shutdown temperature	T_{TSD}		150	175	200	$^{\circ}C$
Thermal hysteresis	T_{HYST}			20		$^{\circ}C$
Current limit reset temperature	T_R			135		$^{\circ}C$
Dynamic temperature	ΔT_{J_SD}	$T_J = -40^{\circ}C$		60		$^{\circ}C$
Turn-off output voltage clamp	V_{DEMAG}	$I_{OUT}=2A, L=6mH,$ $T_J = -40^{\circ}C$ to $150^{\circ}C$	V_S-68	V_S-73		V
OFF-state diagnostic						
Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
OFF-state open load voltage detection threshold	V_{OL}	$V_{IN}=0V$	2	3.5	5	V
OFF-state output sink current	$I_{L(off2)}$	$V_S=48V, V_{IN}=0V, V_{OUT}=V_{OL},$ $T_J = -40^{\circ}C$ to $150^{\circ}C$		-60		μA
OFF-state diagnostic delay time from falling edge of IN	t_{DSTKON}	$V_{DEN}=5V, V_{OUT}=5V, V_{IN}=5V$ to $0V$	150	400	800	μs

Note8: Except for the special test instructions, all electrical parameters are tested under $T_A = +25^{\circ}C$. The minimum and maximum specification range of the specifications is guaranteed by the test, and the typical values are guaranteed by the design, test, or statistical analysis.

Switching Status and Timing Relationship

Switching time and pulse skew



T_{DSTKON}

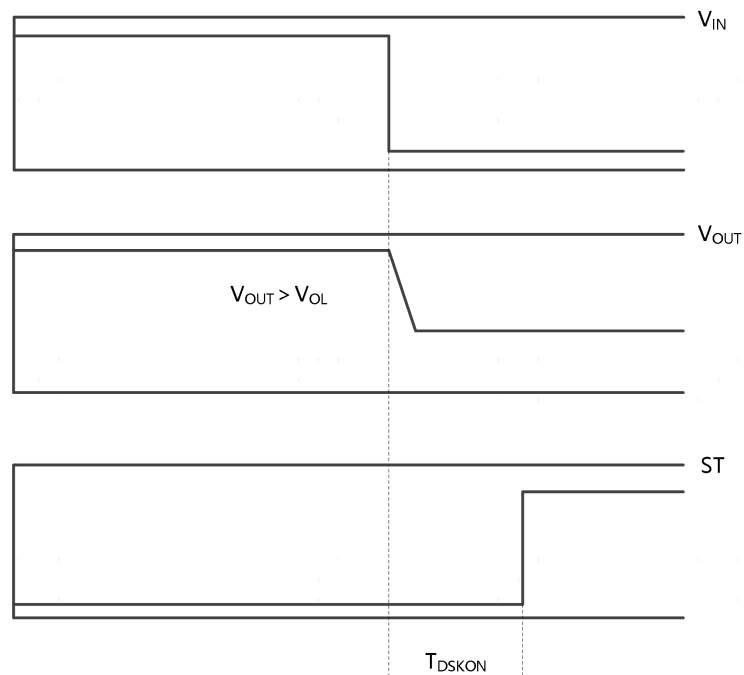
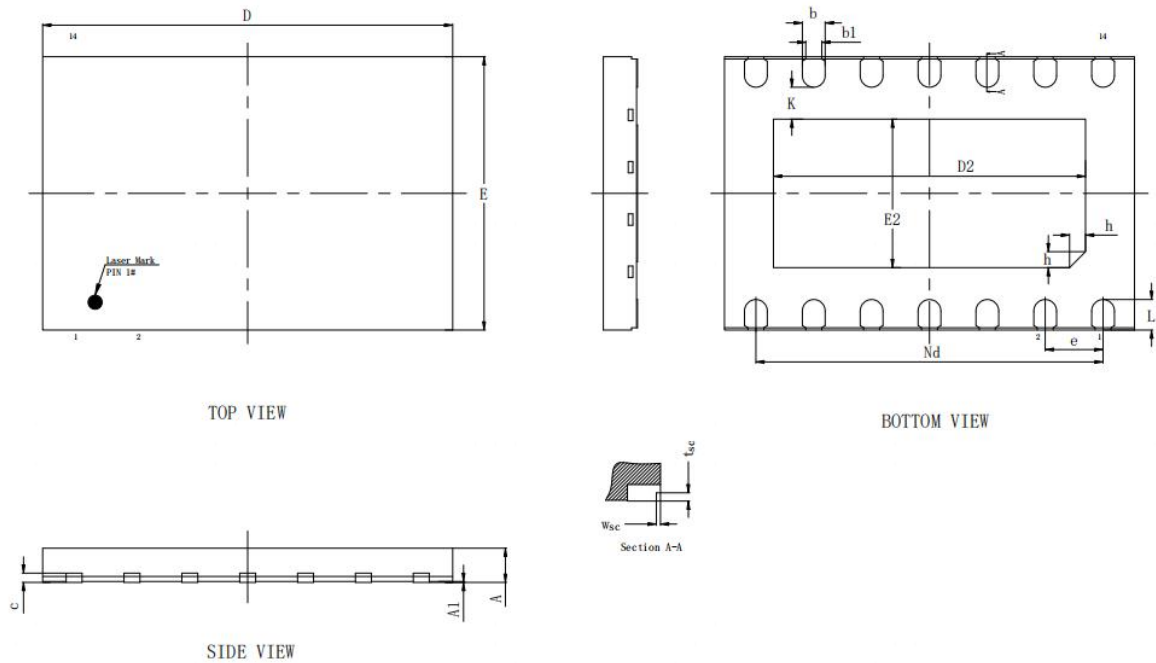


Table 2. Truth table

Conditions	IN	OUT	ST
Normal	L	L	L
	H	H	L
Over Temperature	H	L	H
Open-Load	L	H	H

Package Outline

DFN9×6-14L



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	0.70	0.75	0.80
A1	0	0.02	0.05
b	0.45	0.50	0.55
b1	0.35REF		
c	0.203REF		
D	8.90	9.00	9.10
D2	6.75	6.85	6.95
e	1.27BSC		
Nd	7.62BSC		
E	5.90	6.00	6.10
E2	3.16	3.26	3.36
L	0.62	0.67	0.72
h	0.30	0.35	0.40
K	0.70REF		
W _{sc}	0.01	-	0.09
t _{sc}	0.08	-	0.18

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